

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	5	((("6566722") or ("6611037")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/06/09 13:46
S2	0	S1 and substrate and well and "conductive type" and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:49
S3	0	S1 and substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:49
S4	69	substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:49
S5	0	substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon and "epitaxial silicon" and buffer and photodiode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:50
S6	17	substrate and well and p-type and n-type and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon and "epitaxial silicon" and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:51
S7	663	substrate and well and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:52
S8	74	substrate and well and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer and photodiode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:01

S9	53	substrate and well and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer and photodiode and (STI or LOCOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:05
S10	9	substrate and "well region" and (p-type or n-type) and isolat\$4 and photosensitive and trench\$4 and dop\$4 and anneal and junction and cvd and polysilicon or ("epitaxial silicon") and buffer and photodiode and (STI or LOCOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:06